

HFA40HF60 PD-20381E

Ultrafast, Soft Recovery Diode Surface Mount (SMD-1) 600V, 22A

Features

- Single diode configuration
- Reduced RFI and EMI
- Reduced snubbing
- Extensive characterization of recovery parameters
- Hermetic package
- Surface mount
- ESD Rating: Class 3B per MIL-STD-750, Method 1020

Product Summary

V_R:600V

• **V**_F: 1.75V

• **t**_{rr}: 97ns

• **di**_{(rec)M}/**dt**: 270A/μs

Potential Applications

- DC-DC converter
- Motor drives

Product Validation

Qualified according to MIL-PRF-19500 for space applications



Description

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and di/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motor drives and other applications where switching losses are significant portion of the total losses.

Ordering Information

Table 1 Ordering options

	0.	
Part number	Package	Screening Level
HFA40HF60	SMD-1	COTS
HFA40HF60SCV	SMD-1	JANTXV-equivalent
HFA40HF60SCX	SMD-1	JANTX-equivalent
HFA40HF60SCS	SMD-1	S-level

HFA40HF60

FRED Ultrafast, Soft Recovery Diode



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Absolute Maximum Ratings

1 Absolute Maximum Ratings

Table 2 Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V_R	DC Reverse Voltage	600	V
I _F	Continuous Forward Current, T _C =100 °C ¹	22	Α
I _{FSM}	Single pulse Forward Current, T _c = 25°C ²	225	Α
$P_D @ T_C = 25^{\circ}C$	Maximum Power Dissipation	83	W
T _J T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
Wt	Weight	2.6 (Typical)	g

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 $^{^{1}}$ DC = 50% rect. wave

 $^{^2}$ ½ sine wave, 60 Hz, Pulse width = 8.33 ms



Device Characteristics

2 Device Characteristics

2.1 Electrical Characteristics

Table 3 Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
V_{BR}	Cathode Anode Breakdown Voltage	600	_	_	V	I _R = 100μA
	Forward Voltage Drop See Fig. 1	_	_	1.61		I _F = 22A, T _J = -55°C
V		_	1.63	1.75	V	I _F = 22A, T _J = 25°C
V_F		_	2.07	2.25	V	I _F = 45A, T _J = 25°C
		_	1.52	1.64		I _F = 22A, T _J = 125°C
	Reverse Leakage Current	_	_	10	μΑ	$V_R = V_R$ Rated
I_R	See Fig. 2	_	_	1.0	mA	V _R = 480V, T _J = 125°C
Ст	Junction Capacitance See Fig. 3	_	56	59	pF	V _R = 200V, f = 1.0MHz
Ls	Series Inductance	_	5.9	_	nH	Measured from center of cathode pad the center of anode pad

2.2 Dynamic Recovery Characteristics

Table 4 Dynamic Recovery Characteristics @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Тур.	Мах.	Unit	Test Condition	S
t _{rr1}	Reverse Recovery Time	_	60	97		T _J = 25°C	
t _{rr2}	See Fig. 5	_	110	_	ns	T _J = 125°C	I _F = 22A
I _{RRM1}	Peak Recovery Current	_	5.2	_		T _J = 25°C	
I _{RRM2}	See Fig. 6	_	8.5	_	A	T _J = 125°C	V _R = 200V
Q _{rr1}	Reverse Recovery Charge	_	190	_		T _J = 25°C	
Q _{rr2}	See Fig. 7	_	560	_	nC	T _J = 125°C	$d_{if}/dt = 200 A/ \mu s$
$di_{(rec)M}/dt_1$	Peak Rate of Fall of Recovery	_	270	_		T _J = 25°C	
$di_{(rec)M}/dt_2$	Current During t₀ See Fig. 8	_	170	_	A/ μs	T _J = 125°C	

2.3 Thermal-Mechanical Characteristics

Table 5 Thermal-Mechanical Characteristics

Symbol	Parameter		Max.	Unit
$R_{ heta JC}$	Junction to Case, Single Leg Conducting	_	1.5	°C/W



Electrical Characteristics Curves

3 Electrical Characteristics Curves

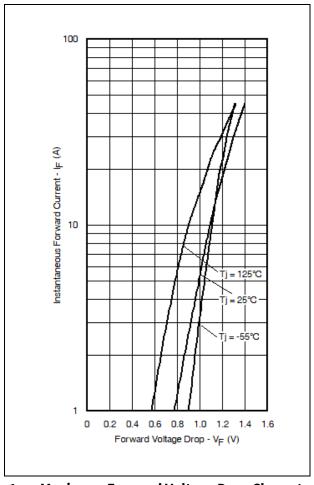


Figure 1 Maximum Forward Voltage Drop Characteristics

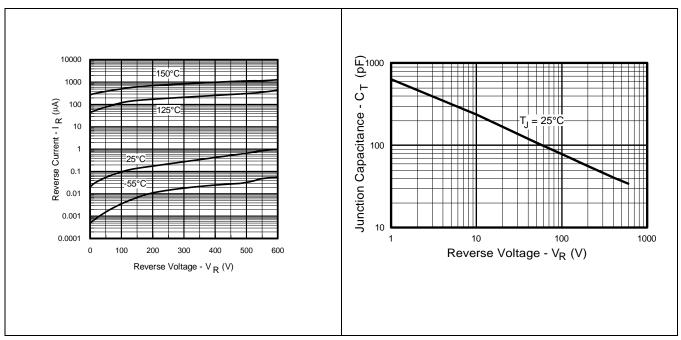


Figure 2 Typical Values of Reverse Current Vs. Reverse Voltage

Figure 3

Typical Junction Capacitance Vs. Reverse Voltage



Electrical Characteristics Curves

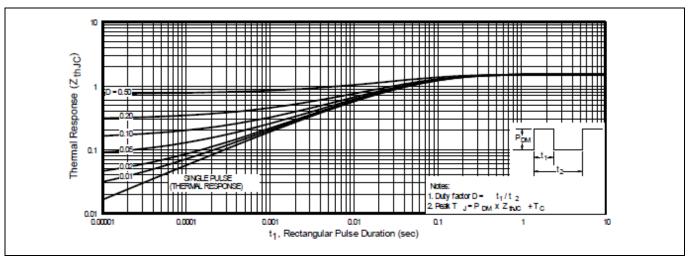


Figure 4 Maximum Thermal Impedance Z_{thJC} Characteristics

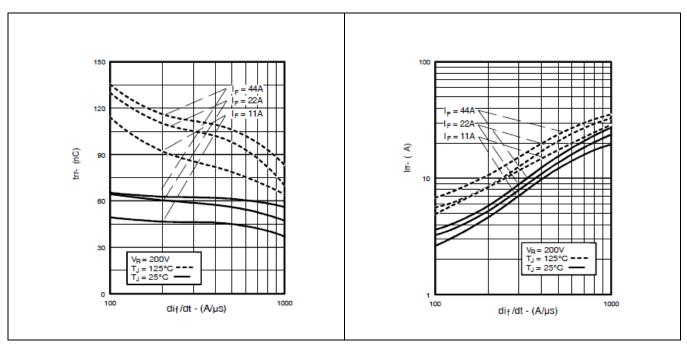


Figure 5 Typical Reverse Recovery Vs. di_f/dt Figure 6 Typical Recovery Current Vs. di_f/dt

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Electrical Characteristics Curves

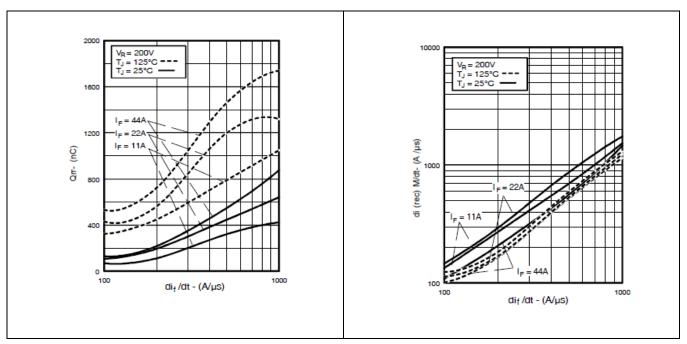


Figure 7 Typical Stored Charge Vs. di_f/dt

Figure 8 Typical di_{(rec)M}/dt Vs. di_f/dt



Test Circuit

4 Test Circuit

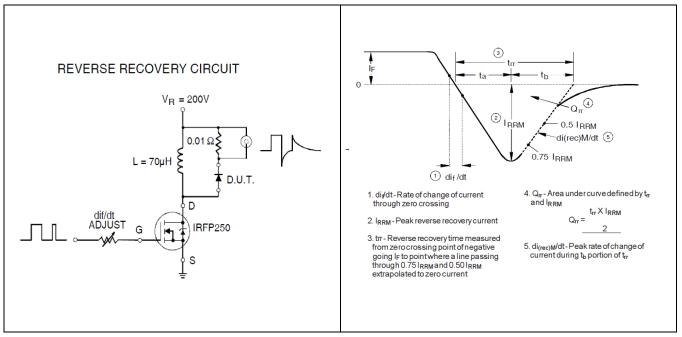


Figure 9 Reverse Recovery Parameter Test Circuit

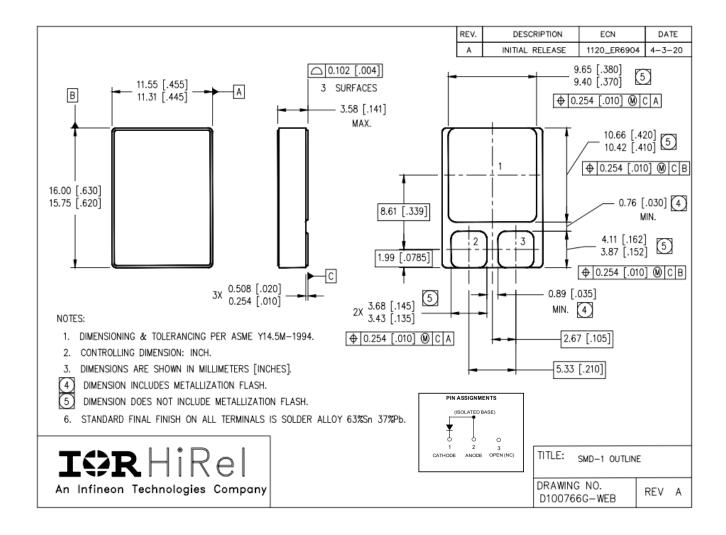
Figure 10 Reverse Recovery Waveform and Definitions



Package Outline

5 Package Outline

Note: For the most updated package outline, please see the website: **SMD-1**



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Revision history

Revision history

Document version	Date of release	Description of changes
	6/30/1999	Final datasheet (PD-20381)
Rev A	04/10/2010	Updated per ECN-17456
Rev B	03/04/2013	Updated per ECN-1120-0911
Rev C	10/14/2016	Updated per ECN-1120-04754
Rev D	06/02/2022	Updated per ECN-1120-08972
Rev E	08/02/2023	Updated per ECN-1120-09610

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